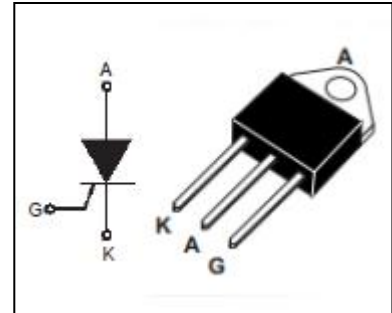


isc Thyristors
BTW69-1200
APPLICATIONS

- Available in high power packages, BTW69 Series is suitable in applications where power handling and power dissipation are critical, such as solid state relays, welding equipment, high power motor
- Minimum Lot-to-Lot variations for robust device performance and reliable operation


ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

SYMBOL	PARAMETER	MIN	UNIT
V _{DRM}	Repetitive peak off-state voltage	1200	V
V _{RDM}	Repetitive peak reverse voltage	1200	V
I _{T(AV)}	Average on-state current, T _c =70° C	31	A
I _{T(RMS)}	RMS on-state current T _c =70° C	50	A
I _{TSM}	Surge non-repetitive on-state current	500	A
P _{G(AV)}	Average gate power dissipation	1	W
T _j	Operating junction temperature	-40~125	°C
T _{stg}	Storage temperature	-40~150	°C

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I _{RRM}	Repetitive peak reverse current	V _{RM} =V _{RDM}	T _j =25°C	10	μA
			T _j =125°C	5	mA
I _{DRM}	Repetitive peak off-state current	V _{DM} =V _{DRM}	T _j =25°C	10	μA
			T _j =125°C	5	mA
V _{TM}	On-state voltage	I _{TM} = 100A		1.6	V
I _{GT}	Gate-trigger current	V _D = 12 V; R _L = 33 Ω		50	mA
V _{GT}	Gate-trigger voltage	V _D = 12 V; R _L = 33 Ω		1.3	V
R _{th(j-c)}	Thermal resistance	Junction to case		0.45	°C/W